

PQMD12

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

8 July 2015

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistors (RET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Low package height of 0.37 mm
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------|---------------------------|---------------------------|---|-----|-----|-----|------|
| Per transis | tor; for the PNP transis | or with negative polarity | , | | | | , |
| V _{CEO} | collector-emitter voltage | open base | | - | - | 50 | V |
| Io | output current | | | - | - | 100 | mA |
| Per transis | tor; for the PNP transis | or with negative polarity | , | | ' | ' | |
| R1 | resistance 1 | T _{amb} = 25 °C | | 33 | 47 | 61 | kΩ |
| R2/R1 | resistance ratio | | | 8.0 | 1 | 1.2 | |



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|------------------------|---|--------------------------|
| 1 | GND1 | GND (emitter) TR1 | 500 | O1 I2 GND2 |
| 2 | I1 | input (base) TR1 | $\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \\ \end{bmatrix}$ | |
| 3 | O2 | output (collector) TR2 | 2 5 | R1 |
| 4 | GND2 | GND (emitter) TR2 | | TR1 TR2 |
| 5 | 12 | input (base) TR2 | 3 4 | R2 R1 |
| 6 | O1 | output (collector) TR1 | Transparent top view | |
| 7 | O1 | output (collector) TR1 | DFN1010B-6 (SOT1216) | GND1 I1 O2 aaa-007379 |
| 8 | O2 | output (collector) TR2 | | dad 557575 |

6. Ordering information

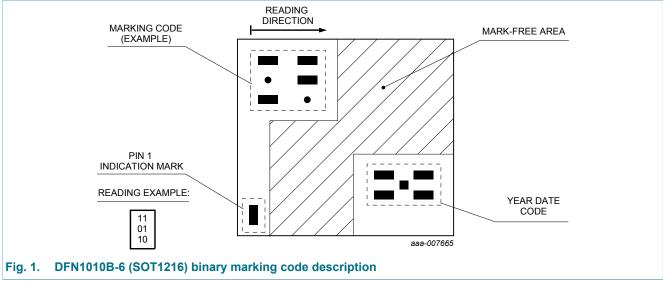
Table 3. Ordering information

| Type number | Package | | | | |
|-------------|------------|--|---------|--|--|
| | Name | Description | Version | | |
| PQMD12 | DFN1010B-6 | DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1216 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PQMD12 | 11 00 00 |



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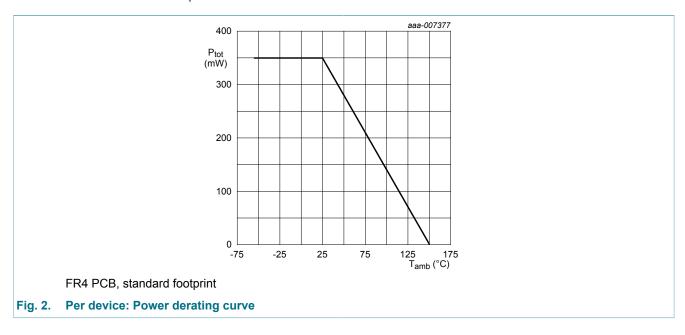
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|----------------------------------|--------------------------------------|-----|-----|-----|------|
| Per transis | tor; for the PNP transistor with | negative polarity | ' | | | |
| V_{CBO} | collector-base voltage | open emitter | | - | 50 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | 50 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | 10 | V |
| VI | input voltage | TR1; positive | | - | 40 | V |
| | | TR1; negative | | - | -10 | V |
| | | TR2; positive | | - | 10 | V |
| | | TR2; negative | | - | -40 | V |
| I _O | output current | | | - | 100 | mA |
| I _{CM} | peak collector current | t _p ≤ 1 ms; single pulse; | | - | 100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 230 | mW |
| Per device | | | | | ' | , |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 350 | mW |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|---|-------------|-----|-----|-----|-----|------|
| Per transisto | r | | | | | | |
| $R_{\text{th(j-a)}}$ | thermal resistance from junction to ambient | in free air | [1] | - | - | 543 | K/W |
| Per device | | | | | | | |
| $R_{\text{th(j-a)}}$ | thermal resistance from junction to ambient | in free air | [1] | - | - | 357 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

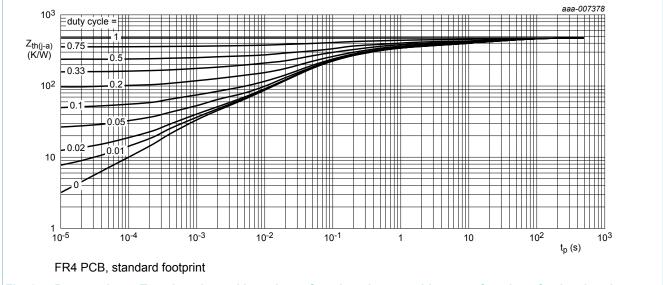


Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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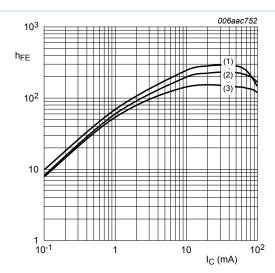
10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------|---|--|-----|-----|-----|-----|------|
| Per transis | tor; for the PNP transistor | with negative polarity | | | | ' | |
| I _{CBO} | collector-base cut-off current (emitter open) | $V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ | | - | - | 100 | nA |
| I _{CEO} | collector-emitter cut-off | V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C | | - | - | 1 | μΑ |
| | current (base open) | V _{CE} = 30 V; I _B = 0 A; T _{amb} = 150 °C | | - | - | 5 | μA |
| I _{EBO} | emitter-base cut-off current (collector open) | $V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ | | - | - | 90 | μA |
| h _{FE} | DC current gain | V_{CE} = 5 V; I_{C} = 5 mA; T_{amb} = 25 °C | | 80 | - | - | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$ | | - | - | 150 | mV |
| V _{I(off)} | off-state input voltage | V_{CE} = 5 V; I_{C} = 100 μ A; T_{amb} = 25 °C | | - | 1.2 | 0.8 | V |
| V _{I(on)} | on-state input voltage | $V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$ | | 3 | 1.6 | - | V |
| R1 | resistance 1 | T _{amb} = 25 °C | | 33 | 47 | 61 | kΩ |
| R2/R1 | resistance ratio | | | 0.8 | 1 | 1.2 | |
| C _C | collector capacitance | $V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; f = 1 \text{ MHz};$ $T_{amb} = 25 \text{ °C}; TR1 \text{ (NPN)}$ | | - | - | 2.5 | pF |
| | | V_{CB} = -10 V; I_{E} = 0 A; f = 1 MHz; T_{amb} = 25 °C; TR2 (PNP) | | - | - | 3 | pF |
| f _T | transition frequency | V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C; TR1 (NPN) | [1] | - | 230 | - | MHz |
| | | V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C; TR2 (PNP) | [1] | - | 180 | - | MHz |

^[1] Characteristics of built-in transistor

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



$$V_{CE} = 5 V$$

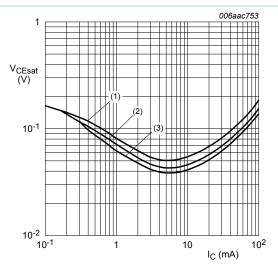
Fig. 4.

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = -40 °C



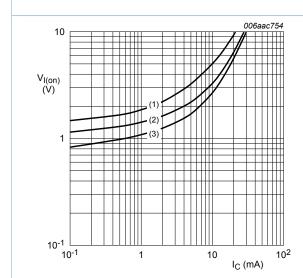


$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -40 \, ^{\circ}C$$



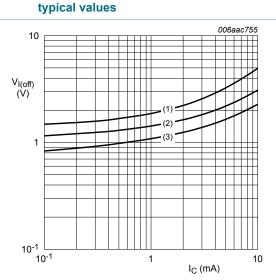
$$V_{CE}$$
 = 0.3 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. NPN transistor: On-state input voltage as a function of collector current; typical values



NPN transistor: Collector-emitter saturation

voltage as a function of collector current;

$$V_{CE} = 5 V$$

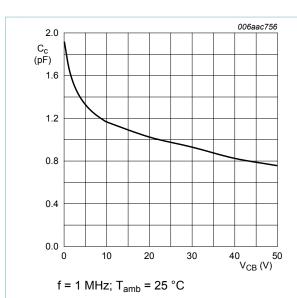
(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

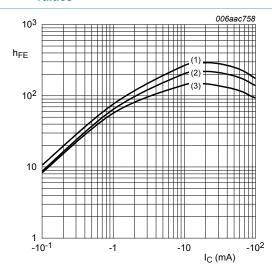
(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. NPN transistor: Off-state input voltage as a function of collector current; typical values

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



NPN transistor: Collector capacitance as a Fig. 8. function of collector-base voltage; typical values



 V_{CE} = -5 V

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

collector current; typical values

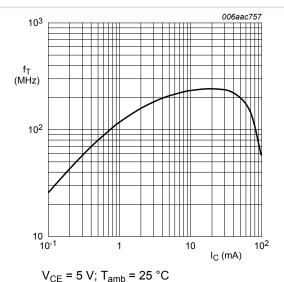
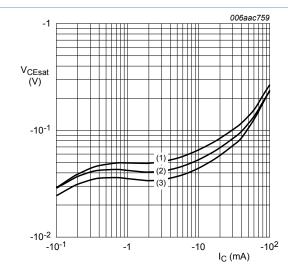


Fig. 9. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



 $I_{\rm C}/I_{\rm B} = 20$

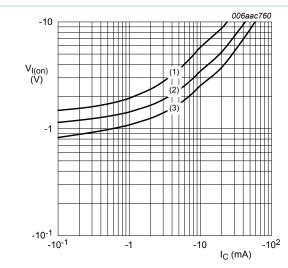
(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. PNP transistor: DC current gain as a function of Fig. 11. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

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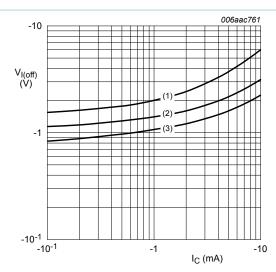
$$V_{CE}$$
 = -0.3 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 12. PNP transistor: On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 13. PNP transistor: Off-state input voltage as a function of collector current; typical values

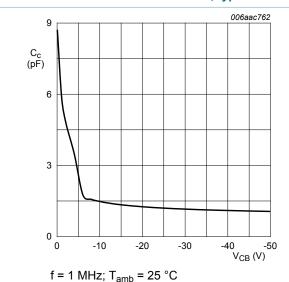


Fig. 14. PNP transistor: Collector capacitance as a function of collector-base voltage; typical

values of built-in transistor

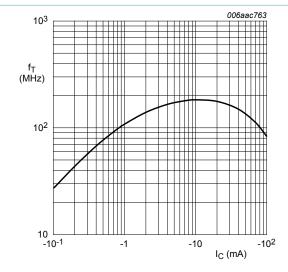


Fig. 15. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

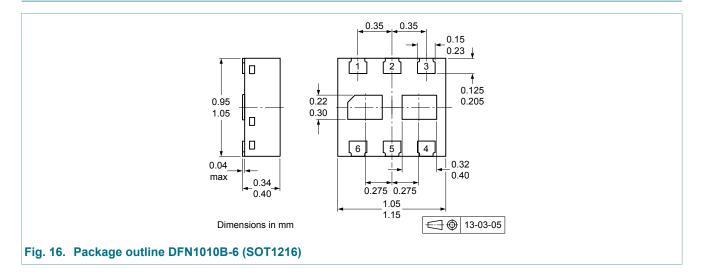
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11. Test information

11.1 Quality information

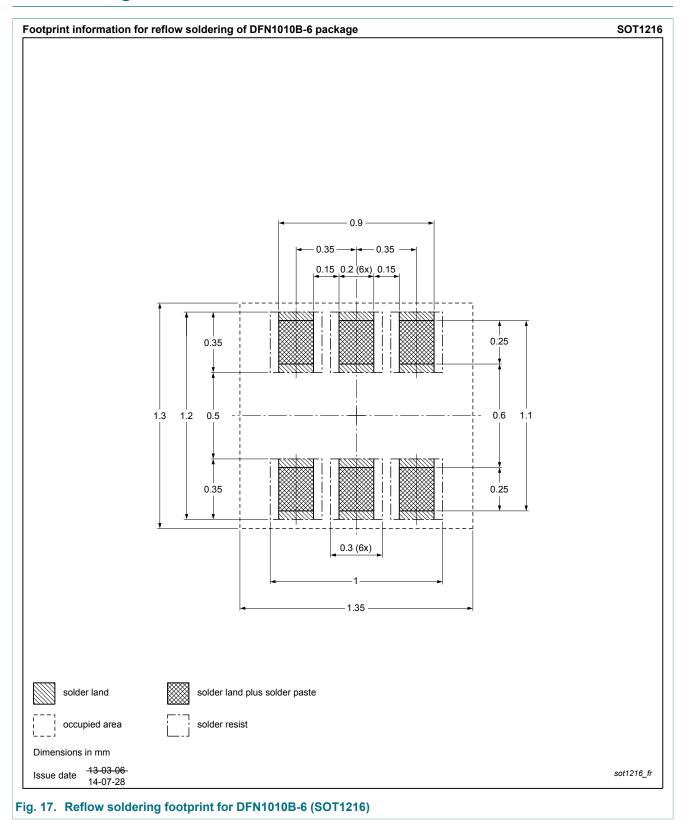
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

13. Soldering



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NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------------|-----------------------|---------------|------------|
| PQMD12 v.2 | 20150708 | Product data sheet | - | PQMD12 v.1 |
| Modification: | Change of binary m | arking code position. | | |
| PQMD12 v.1 | 20130724 | Product data sheet | - | - |

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

15. Legal information

15.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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